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Please cancel claims 1-84

85. A sputtering target comprising Zr and one or more elements selected from the group consisting of Al, B, Ba, Be, Ca, Ce, Co, Cs, Dy, Er, Fe, Gd, Hf, Ho, La, Mg, Mn, Mo, Nb, Nd, Ni, Pr, Sc, Sm, Sr, Ta, V, W, Y, and Yb; the Zr being the majority element of the target.

86. The sputtering target of claim 85 wherein the Zr concentration within the target is at least 70%.

87. The sputtering target of claim 85 wherein the Zr concentration within the target is at least 90%.

88. The sputtering target of claim 85 wherein the Zr concentration within the target is at least 94%.

89. The sputtering target of claim 85 wherein the Zr concentration within the target is at least 97%.

90. The sputtering target of claim 85 wherein the Zr concentration within the target is less than 98%.

91. The sputtering target of claim 85 wherein the total non-zirconium metal content of the target is in a range of from 0.001% to 50% of the ingot.

92. The sputtering target of claim 85 wherein the total non-zirconium metal content of the target is in a range of 0.001% to 10% of the ingot.

93. The sputtering target of claim 85 wherein the total non-zirconium metal content of the target is at least 0.01% of the ingot.

94. The sputtering target of claim 85 wherein the total non-zirconium metal content of the target is at least 0.1% of the ingot.

95. The sputtering target of claim 85 wherein the total non-zirconium metal content of the target is at least 1% of the ingot.

96. The sputtering target of claim 85 wherein the total non-zirconium metal content of the target is at least 2% of the ingot.

97. The sputtering target of claim 85 consisting of Zr and Ti.

98. A sputtering target comprising Zr and Ti; the Zr being the majority element of the target and being present to a concentration within the target of at least 55%.

99. The sputtering target of claim 98 wherein the Zr concentration within the target is at least 70%.

100. The sputtering target of claim 98 wherein the Zr concentration within the target is at least 90%.

101. The sputtering target of claim 98 wherein the Zr concentration within the target is at least 94%.

102. The sputtering target of claim 98 wherein the Zr concentration within the target is at least 97%.

103. The sputtering target of claim 98 wherein the Zr concentration within the target is less than 98%.

104. A sputtering target comprising Ti and B; the Ti being the majority element of the target.

105. The sputtering target of claim 104 wherein the Ti concentration within the target is at least 70%.

106. The sputtering target of claim 104 wherein the Ti concentration within the target is at least 90%.

107. The sputtering target of claim 104 wherein the Ti concentration within the target is at least 94%.

108. The sputtering target of claim 104 wherein the Ti concentration within the target is at least 97%.

109. The sputtering target of claim 108 wherein the B content of the target is greater than 5 ppm.

110. The sputtering target of claim 108 wherein the B content of the target is greater than 50 ppm.

111. The sputtering target of claim 108 wherein the B content of the target is greater than 500 ppm.

112. The sputtering target of claim 108 wherein the B content of the target is greater than one part per thousand.

113. The sputtering target of claim 104 wherein the Ti concentration within the target is less than 98%.

114. The sputtering target of claim 104 wherein the B content of the target is greater than 5 ppm.

115. The sputtering target of claim 104 wherein the B content of the target is greater than 50 ppm.

116. The sputtering target of claim 104 wherein the B content of the target is greater than 500 ppm.

117. The sputtering target of claim 104 wherein the B content of the target is greater than one part per thousand.

118. The sputtering target of claim 104 consisting of Ti and B.